THE DATASHEET OF

SI3499DV-T1-E3

www.win-source.net 0086-755-83957316

P-Channel 1.5 V (G-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 8	0.023 at V_{GS} = - 4.5 V	- 7	28
	0.029 at V_{GS} = - 2.5 V	- 6.2	
	0.036 at V_{GS} = - 1.8 V	- 5.2	
	0.048 at V_{GS} = - 1.5 V	- 5	

FEATURES

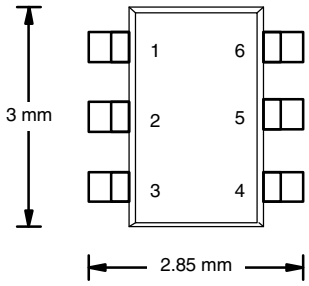
- **Halogen-free According to IEC 61249-2-21 Definition**
- TrenchFET® Power MOSFET: 1.5 V Rated
- Ultra-Low On-Resistance
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

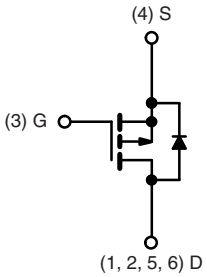
APPLICATIONS

- Load Switch for Portable Devices

TSOP-6
Top View



Ordering Information: Si3499DV-T1-E3 (Lead (Pb)-free)
Si3499DV-T1-GE3 (Lead (Pb)-free and Halogen-free)
Marking Code: 99xxx



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)					
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	- 8		V
Gate-Source Voltage		V_{GS}	± 5		
Continuous Drain Current (T_J = 150 °C)[a]	T_A = 25 °C	I_D	- 7	- 5.3	A
	T_A = 85 °C		- 3.6	- 3.9	
Pulsed Drain Current		I_{DM}	- 20		
Continuous Source Current (Diode Conduction)[a]		I_S	- 1.7	- 0.9	
Maximum Power Dissipation[a]	T_A = 25 °C	P_D	2	1.1	W
	T_A = 85 °C		1	0.6	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 s	R_{thJA}	45	62.5	°C/W
	Steady State		90	110	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	25	30	

Notes:
a. Surface mounted on 1" x 1" FR4 board.

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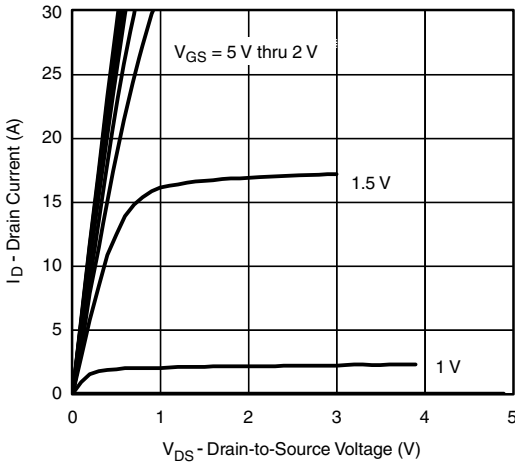
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250 µA	- 0.35		- 0.75	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 5 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 8 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 8 V, V_{GS} = 0 V, T_J = 85 °C			- 10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = - 5 V, V_{GS} = - 4.5 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 7 A		0.019	0.023	Ω
		V_{GS} = - 2.5 V, I_D = - 6.2 A		0.024	0.029	
		V_{GS} = - 1.8 V, I_D = - 5.2 A		0.028	0.036	
		V_{GS} = - 1.5 V, I_D = - 3 A		0.035	0.048	
Forward Transconductance[a]	g_{fs}	V_{DS} = - 5 V, I_D = - 7 A		28		S
Diode Forward Voltage[a]	V_{SD}	I_S = - 1.7 A, V_{GS} = 0 V		- 0.63	- 1.1	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = - 4 V, V_{GS} = - 4.5 V, I_D = - 7 A		28	42	nC
Gate-Source Charge	Q_{gs}			2.9		
Gate-Drain Charge	Q_{gd}			5.8		
Gate Resistance	R_g		4	8.5	13	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 4 V, R_L = 4 Ω $I_D \cong$ - 1 A, V_{GEN} = - 4.5 V, R_g = 6 Ω		27	40	ns
Rise Time	t_r			65	100	
Turn-Off Delay Time	$t_{d(off)}$			210	315	
Fall Time	t_f			110	165	
Source-Drain Reverse Recovery Time	t_{rr}	I_F = - 1.7 A, dI/dt = 100 A/µs		40	70	

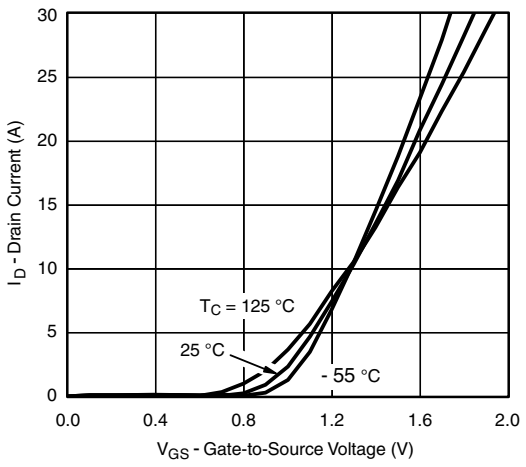
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Output Characteristics



Transfer Characteristics

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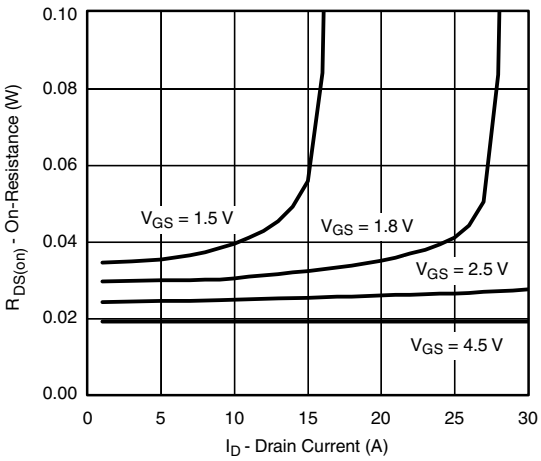
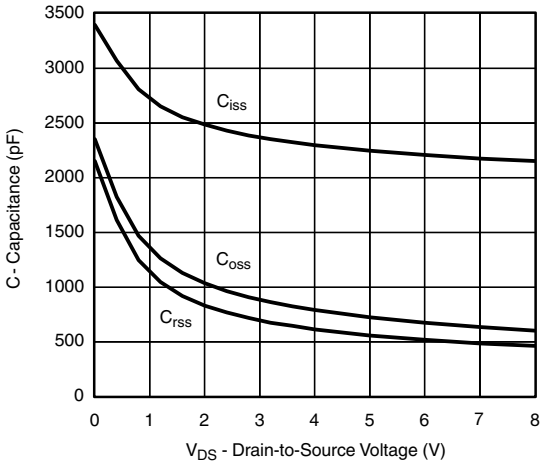
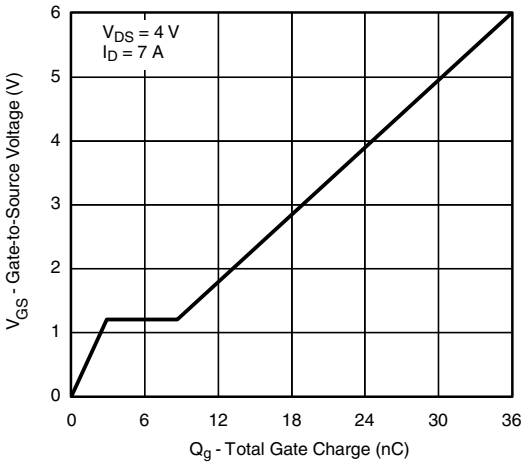


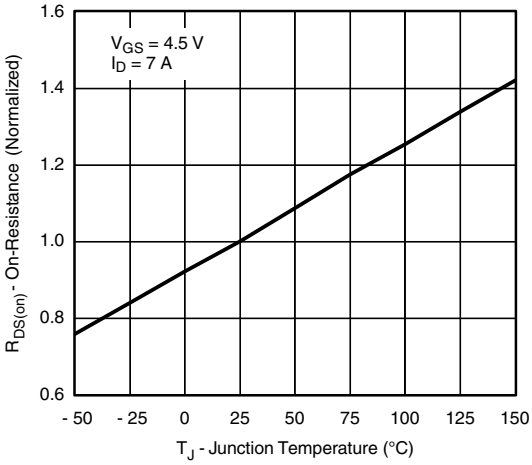
On-Resistance vs. Drain Current



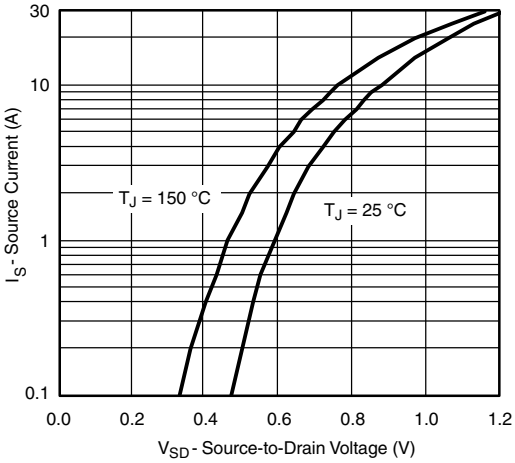
Capacitance



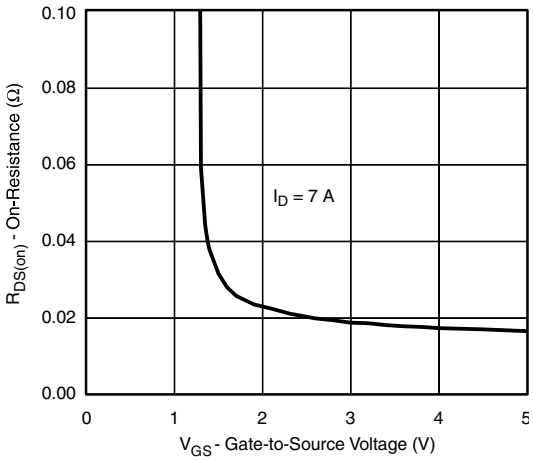
Gate Charge



On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

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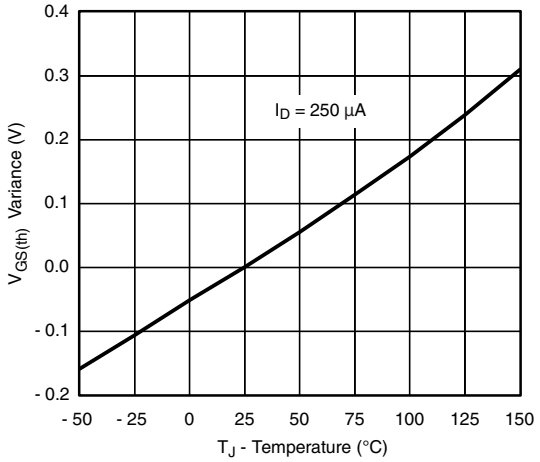
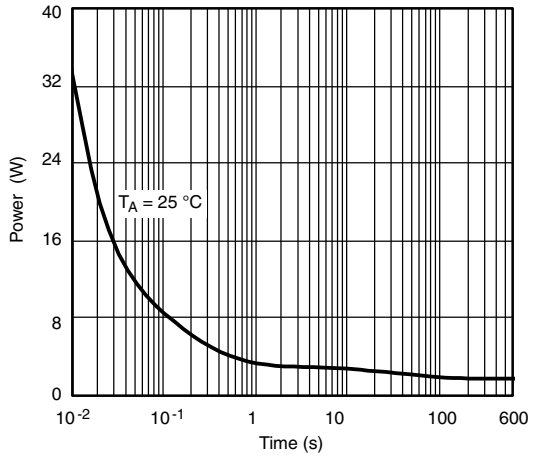
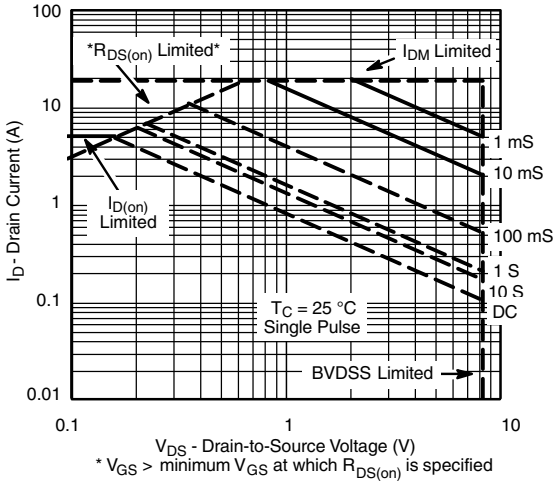


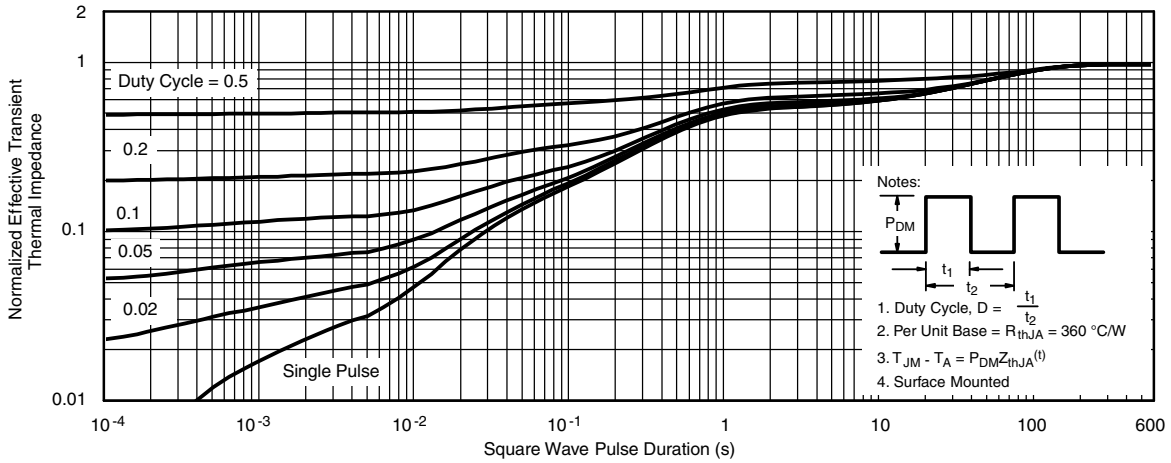
Threshold Voltage



Single Pulse Power



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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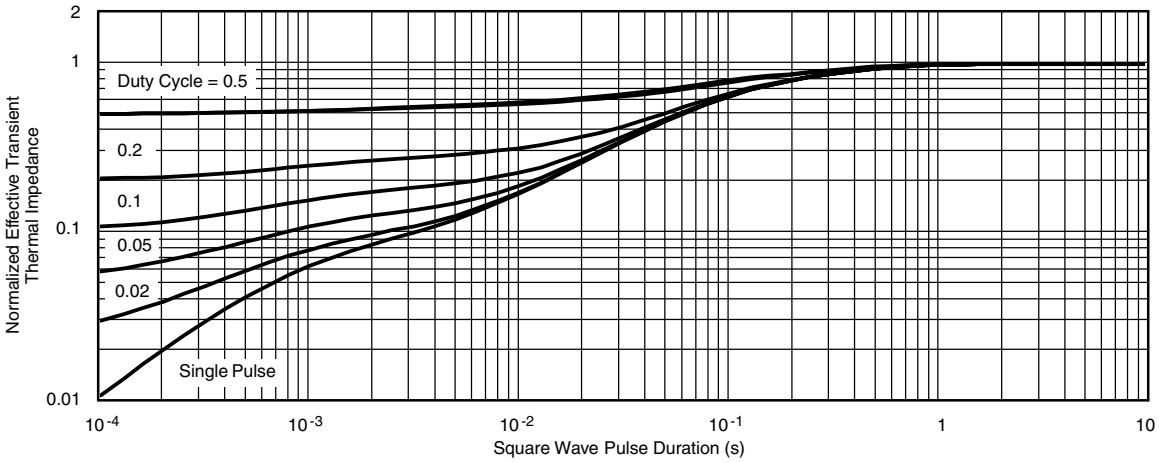

Normalized Thermal Transient Impedance, Junction-to-Foot

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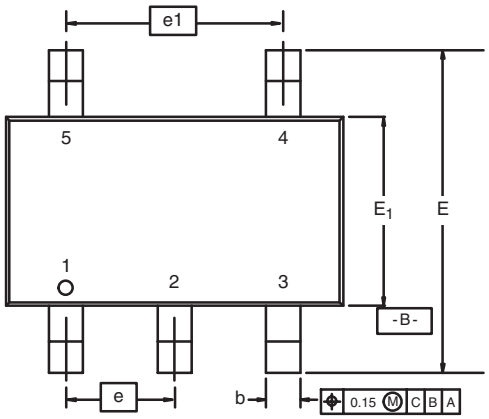
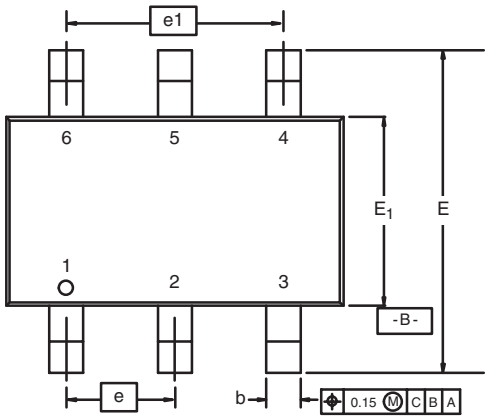
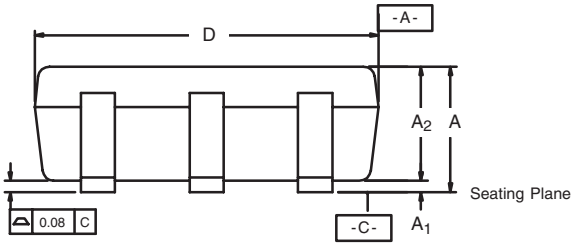
TSOP: 5/6–LEAD
JEDEC Part Number: MO-193C

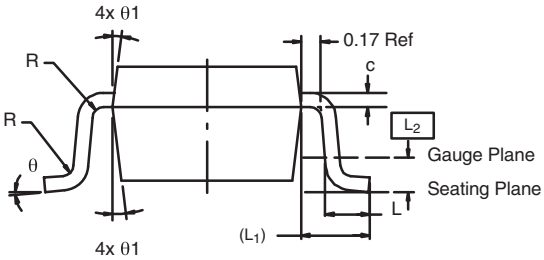


5-LEAD TSOP



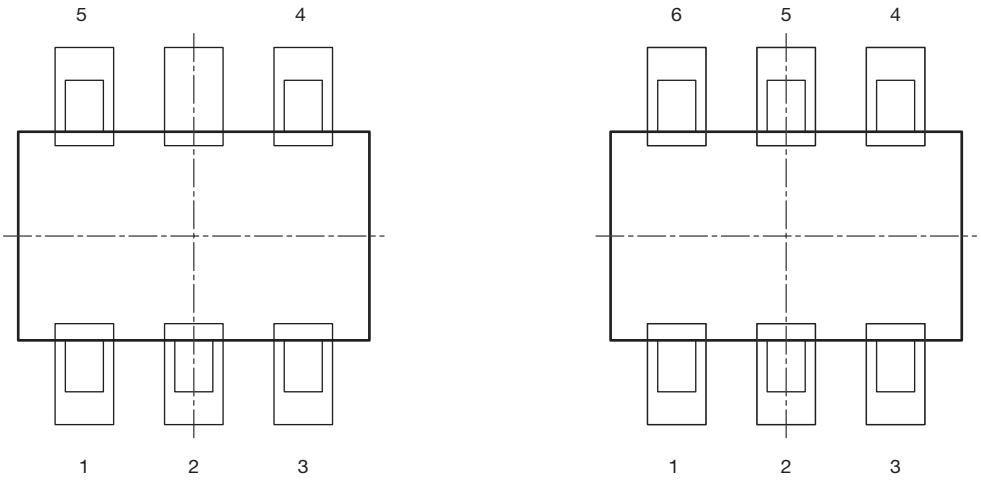
6-LEAD TSOP





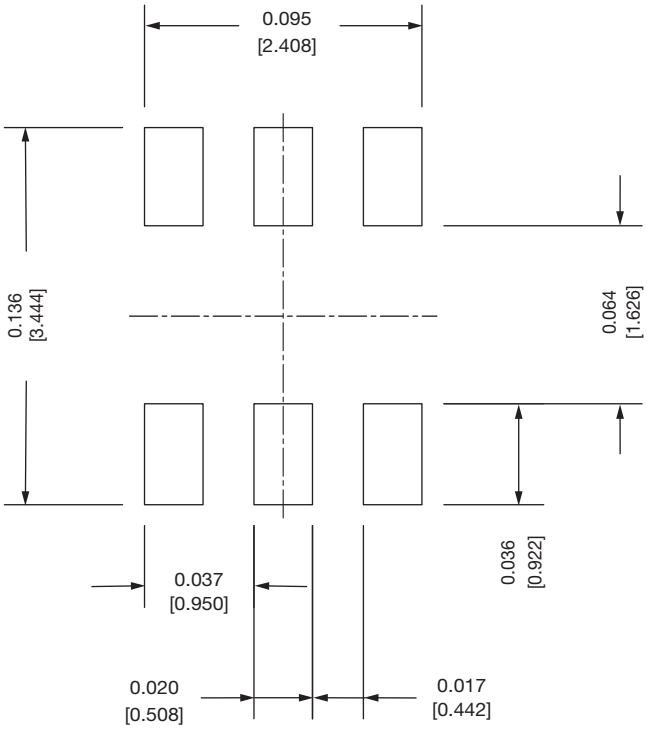
Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.036	-	0.043
A_1	0.01	-	0.10	0.0004	-	0.004
A_2	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E_1	1.55	1.65	1.70	0.061	0.065	0.067
e	0.95 BSC			0.0374 BSC		
e_1	1.80	1.90	2.00	0.071	0.075	0.079
L	0.32	-	0.50	0.012	-	0.020
L_1	0.60 Ref			0.024 Ref		
L_2	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ_1	7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540						

Recommended Land Pattern For TSOP-5L / TSOP-6L



TSOP 5L

TSOP 6L



Note

- All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022
DWG: 3010

For technical questions, contact: pmostechsupport@vishay.com

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